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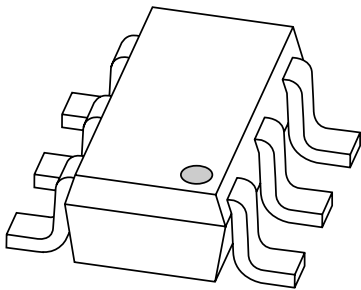
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Kind regards,

Team Nexperia

# DATA SHEET



## **PBSS4240DPN** 40 V low $V_{CEsat}$ NPN/PNP transistor

Product data sheet

2003 Feb 20



# 40 V low $V_{CEsat}$ NPN/PNP transistor

# PBSS4240DPN

### FEATURES

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain  $h_{FE}$  at high  $I_C$
- High efficiency leading to reduced heat generation
- Reduced printed-circuit board area requirements.

### APPLICATIONS

- Power management:
  - Complementary MOSFET driver
  - Dual supply line switching.
- Peripheral driver:
  - Half and full bridge motor drivers
  - Multi-phase stepper motor driver.

### DESCRIPTION

NPN/PNP low  $V_{CEsat}$  transistor pair in a SOT457 (SC-74) plastic package.

### MARKING

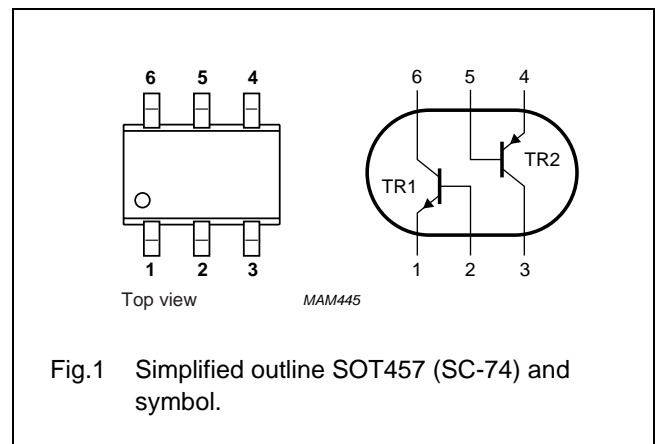
TYPE NUMBER	MARKING CODE
PBSS4240DPN	M3

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.		UNIT
		NPN	PNP	
$V_{CEO}$	emitter-collector voltage	40	-40	V
$I_C$	collector current (DC)	1.35	-1.1	A
$I_{CRP}$	repetitive peak collector current	2	-2	A
$I_{CM}$	peak collector current	3	-3	A
$R_{CEsat}$	equivalent on-resistance	200	260	$m\Omega$

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



40 V low  $V_{CEsat}$  NPN/PNP transistor

## PBSS4240DPN

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor unless otherwise specified; for the PNP transistor with negative polarity</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	40	V
$V_{CEO}$	collector-emitter voltage	open base	–	40	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC) NPN PNP		–	1.35	A
			–	–1.1	A
			–		
$I_{CRP}$	repetitive peak collector current	note 1	–	2	A
$I_{CM}$	peak collector current	single peak	–	3	A
$I_B$	base current (DC)		–	300	mA
$I_{BM}$	peak base current		–	1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 2	–	370	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 3	–	310	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 1	–	1.1	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 2	–	600	mW

**Notes**

- Operated under pulsed conditions: duty cycle  $\delta \leq 20\%$ ; pulse width  $t_p \leq 10\text{ ms}$ ; mounting pad for collector standard footprint.
- Device mounted on a printed-circuit board; single-sided copper; tinplated; mounting pad for collector  $1\text{ cm}^2$ .
- Device mounted on a printed-circuit board; single-sided copper; tinplated; standard footprint.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
<b>Per transistor</b>				
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	340	K/W
		in free air; note 2	110	K/W

**Notes**

- Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector  $1\text{ cm}^2$ .
- Operated under pulsed conditions: pulse width  $t_p \leq 10\text{ ms}$ ; duty cycle  $\delta \leq 0.20$ ; mounting pad for collector standard footprint.

40 V low  $V_{CEsat}$  NPN/PNP transistor

## PBSS4240DPN

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

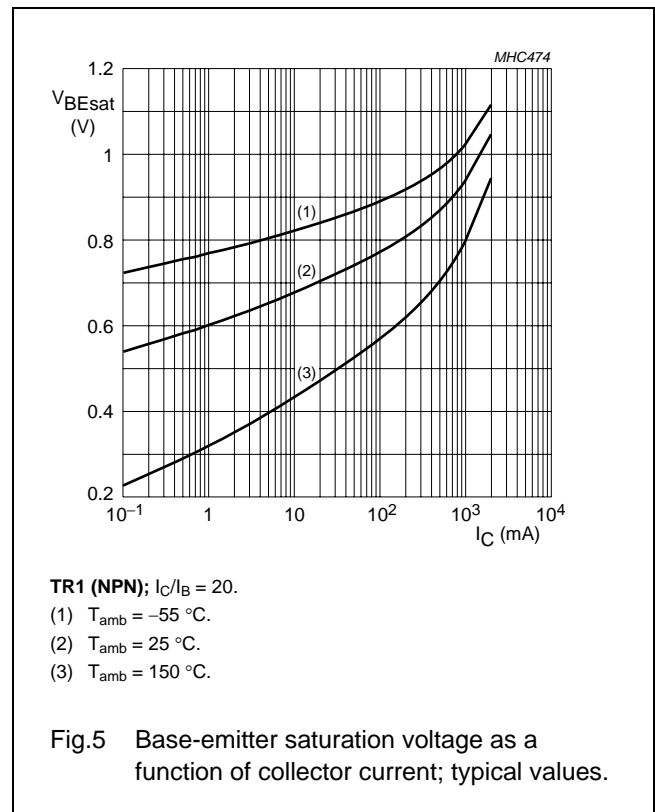
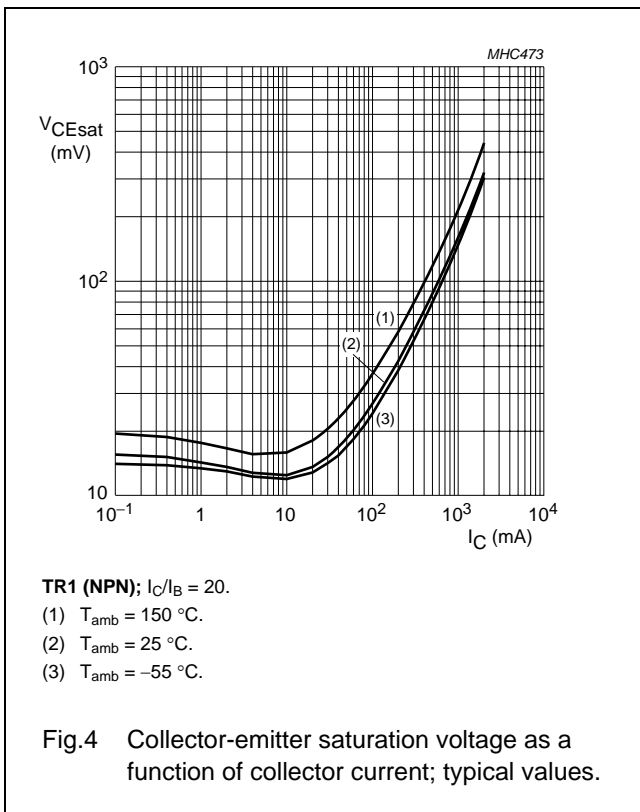
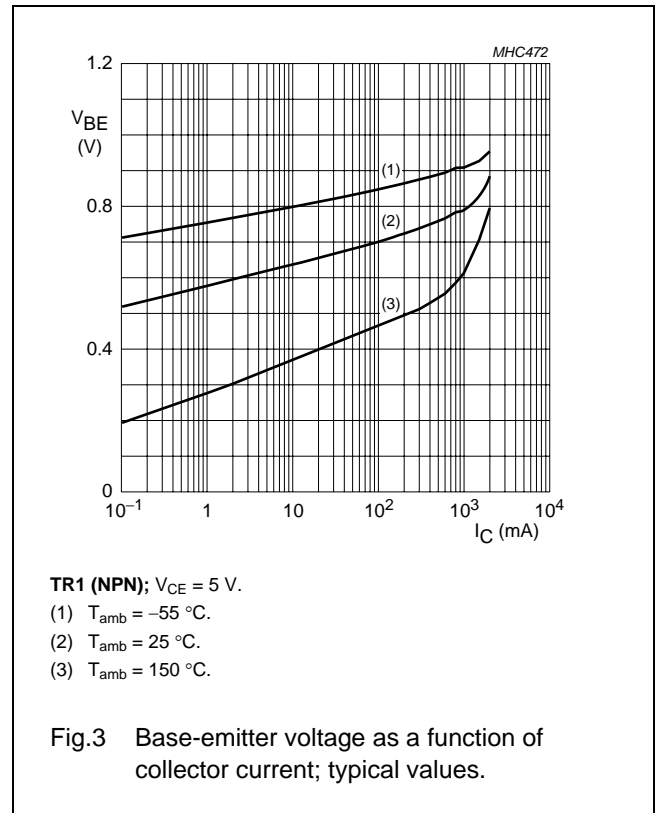
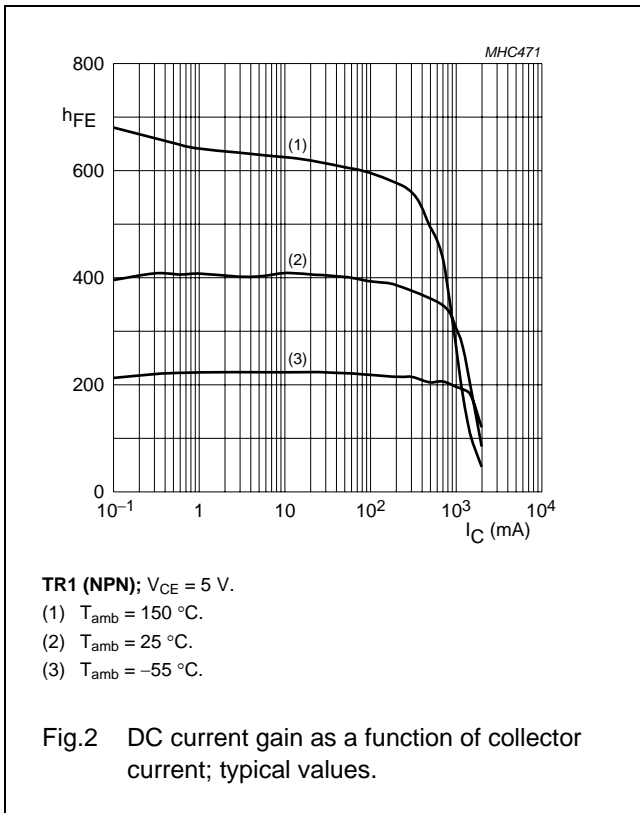
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor unless otherwise specified; for the PNP transistor with negative polarity</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 40\text{ V}; I_E = 0; T_j = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0$	–	–	100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	300	–	–	
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V};$ $f = 100\text{ MHz}$	150	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0;$ $f = 1\text{ MHz}$	–	–	12	pF
<b>TR1 (NPN)</b>						
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	300	–	900	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	200	–	–	
		$V_{CE} = 5\text{ V}; I_C = 2\text{ A};$ note 1	75	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	60	75	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	80	100	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	150	200	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA};$ note 1	–	300	400	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	–	–	1.1	V
$R_{CEsat}$	equivalent on-resistance	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	200	$\text{m}\Omega$
<b>TR2 (PNP)</b>						
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}$	300	–	800	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	250	–	–	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	160	–	–	
		$V_{CE} = -5\text{ V}; I_C = -2\text{ A};$ note 1	50	–	–	
$V_{CEsat}$	saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	-90	-120	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	-100	-145	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	-180	-260	mV
		$I_C = -2\text{ A}; I_B = -200\text{ mA};$ note 1	–	-400	-530	mV
$V_{BEsat}$	saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	-1	V
$R_{CEsat}$	equivalent on-resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA};$ note 1	–	–	260	$\text{m}\Omega$

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

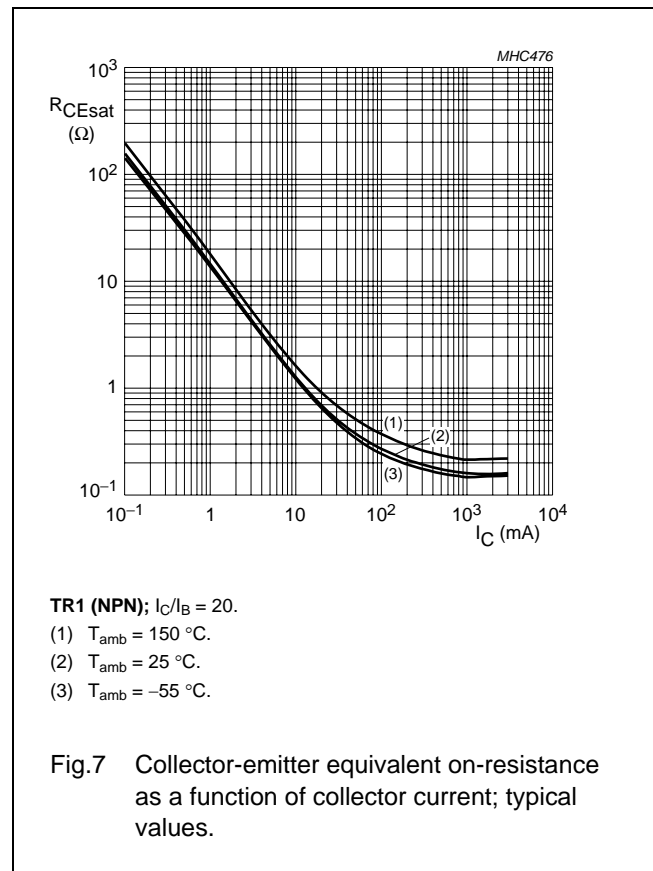
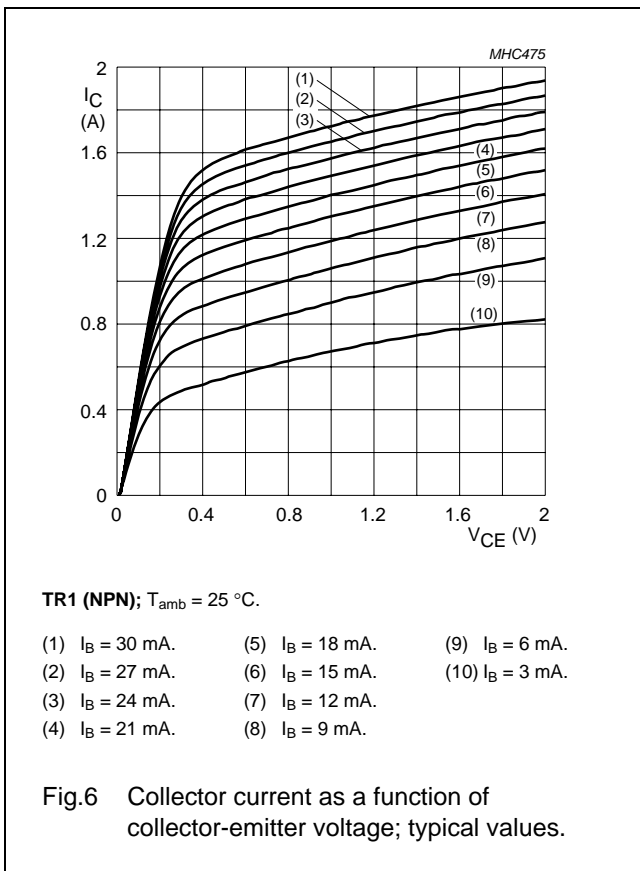
40 V low  $V_{CEsat}$  NPN/PNP transistor

PBSS4240DPN



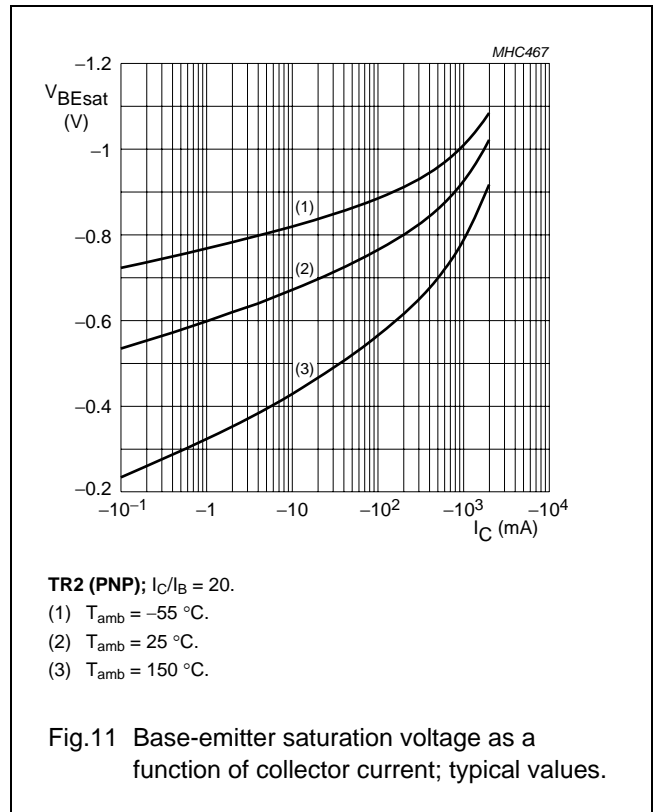
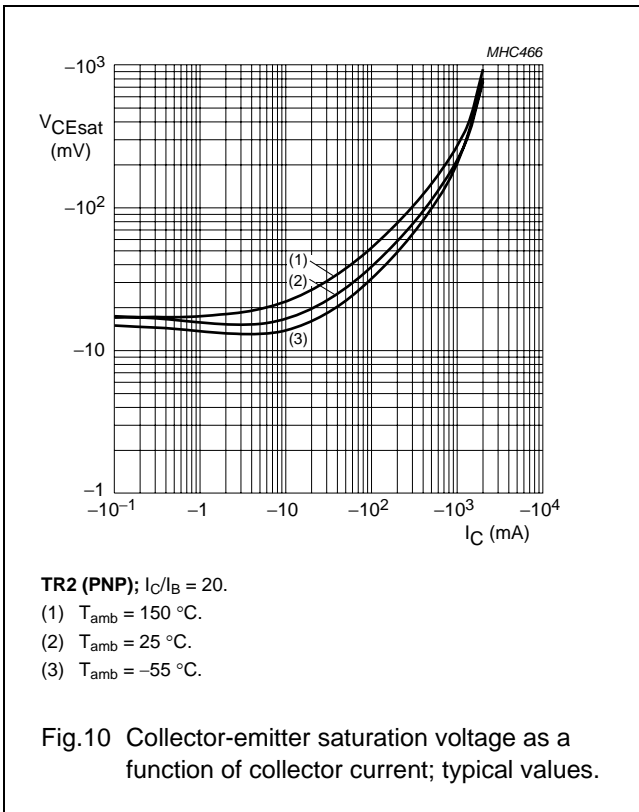
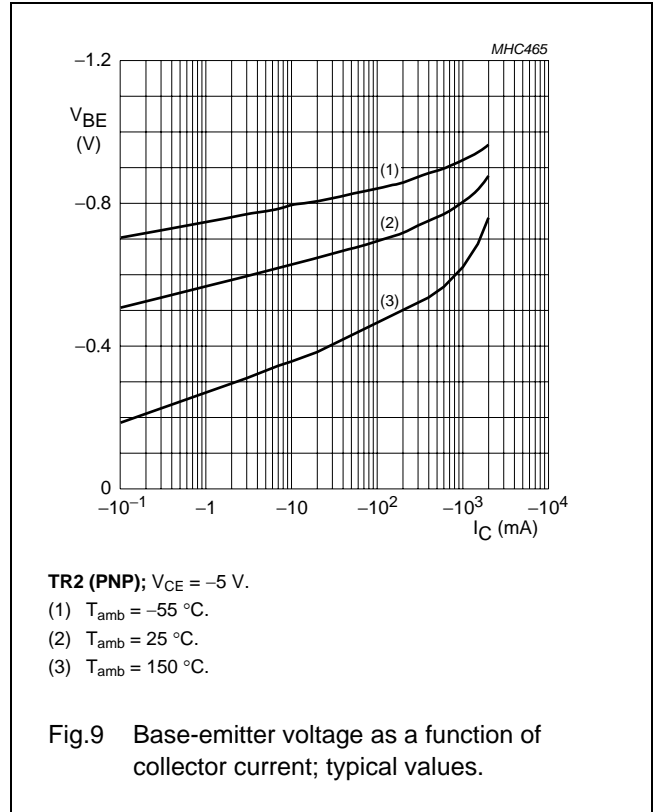
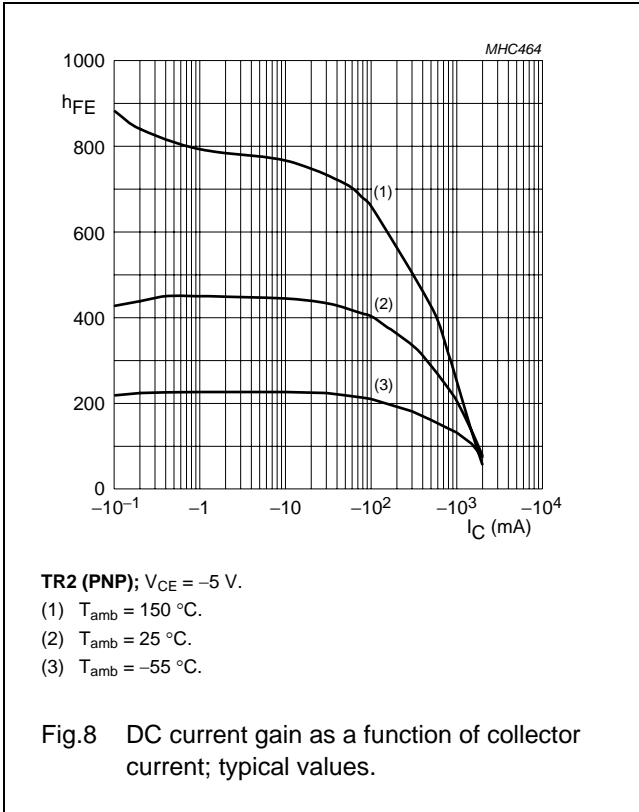
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40 V low  $V_{CEsat}$  NPN/PNP transistor

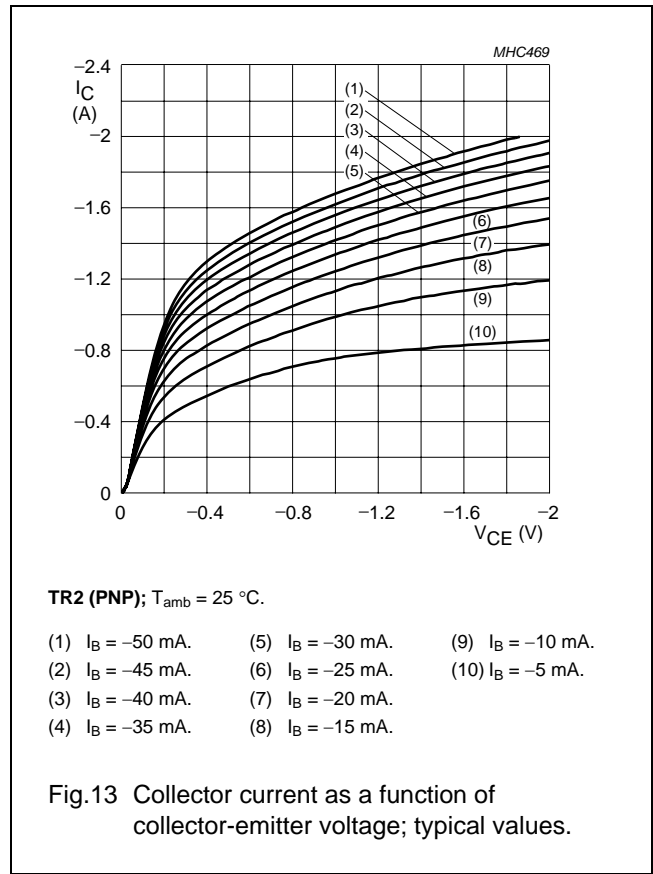
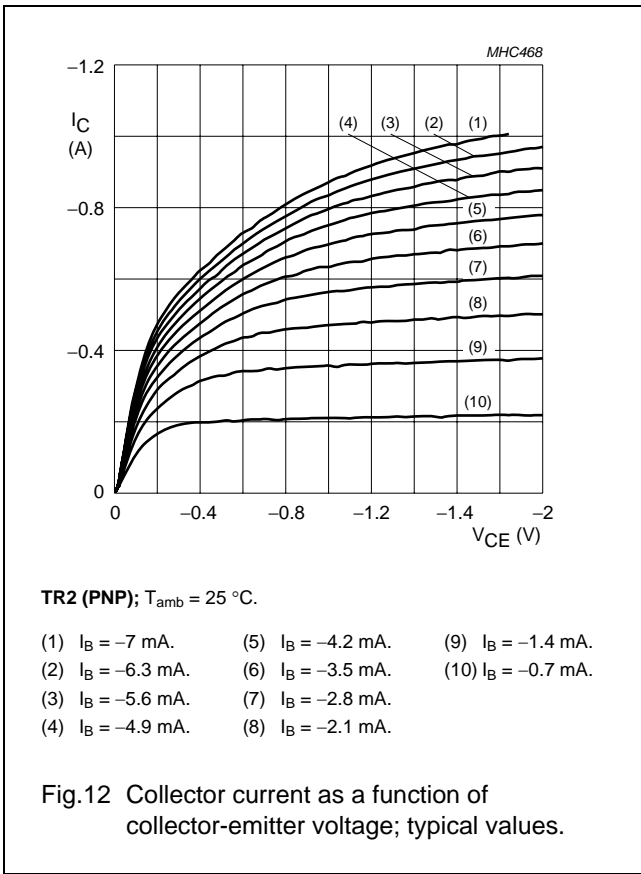
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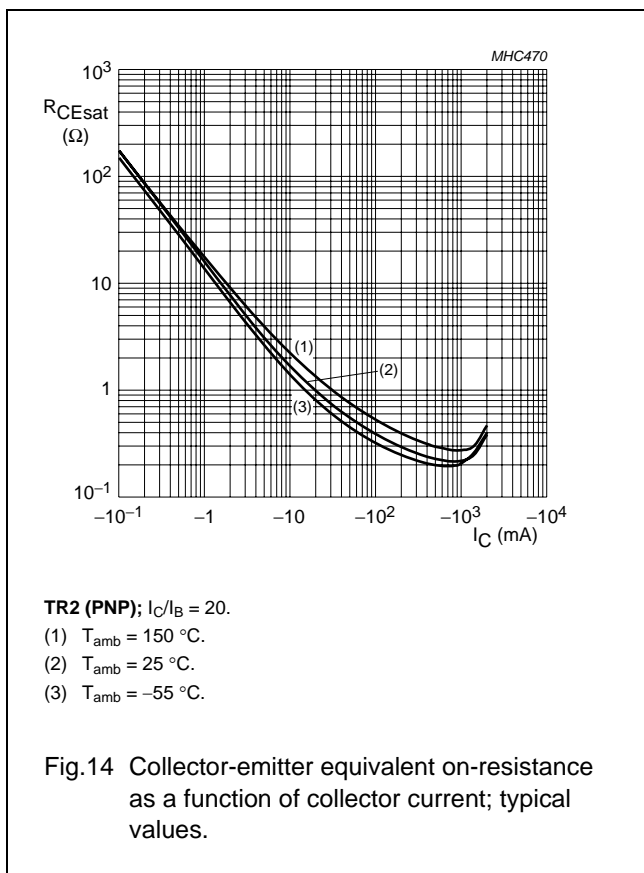
40 V low  $V_{CEsat}$  NPN/PNP transistor

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40 V low  $V_{CEsat}$  NPN/PNP transistor

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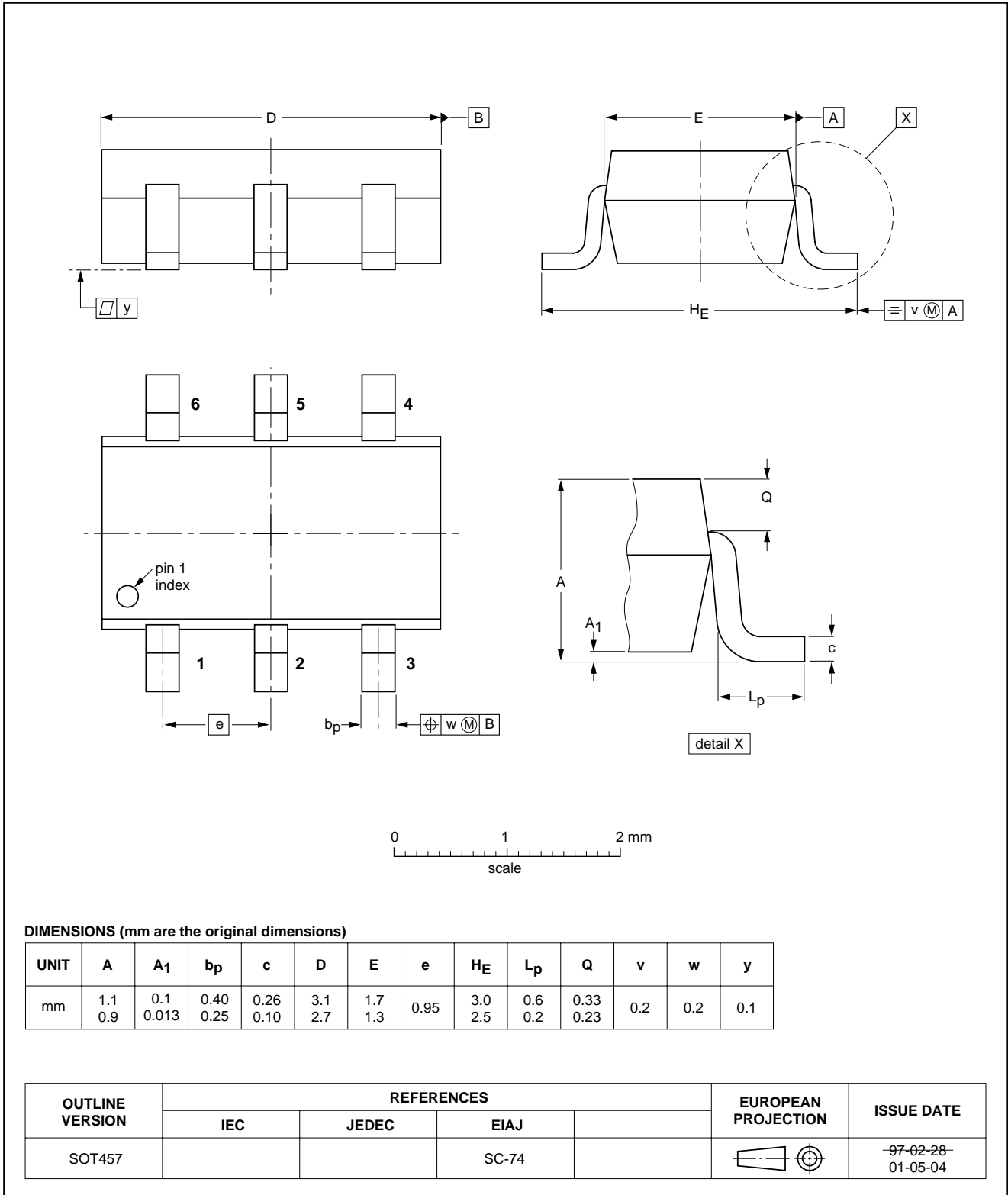
40 V low  $V_{CEsat}$  NPN/PNP transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



40 V low  $V_{CEsat}$  NPN/PNP transistor

PBSS4240DPN

**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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